

X=1490 μm Y=730 μm

Product Features

- ◆ RF frequency: 24 to 32 GHz
- ◆ Noise figure: 2 dB, typical
- ◆ Linear gain: 21 dB, typical
- ◆ P1dB: 7 dBm, typical
- ◆ Unconditionally stable
- ◆ Self-bias design (single supply)
- ◆ DC Power: 5 Vdc at 68 mA

Performance Characteristics (Ta = 25°C)

Specification	Min	Typ	Max	Unit
Frequency	24		32	GHz
Linear Gain	18	21		dB
Noise Figure		2	3	dB
Input Return Loss	10	12		dB
Output Return Loss	5	8		dB
P1dB	5	7		dBm
Vd		5		V
Id		68		mA
Thermal Resistance				C/W

Applications

- ◆ Point-to-Point Digital Radios
- ◆ Point-to-Multipoint Digital Radios
- ◆ VSAT

Product Description

The ALH364 is a broadband, three-stage, self-biased, low noise monolithic HEMT amplifier designed for use in commercial digital microwave radios and wireless LANs. The small die size allows for extremely compact packaging. To ensure rugged and reliable operation, HEMT devices are fully passivated. Both bond pad and backside metallization are Ti/Au, which is compatible with conventional die attach, thermocompression and thermosonic wire bonding assembly techniques.

Absolute Maximum Ratings (Ta = 25°C)

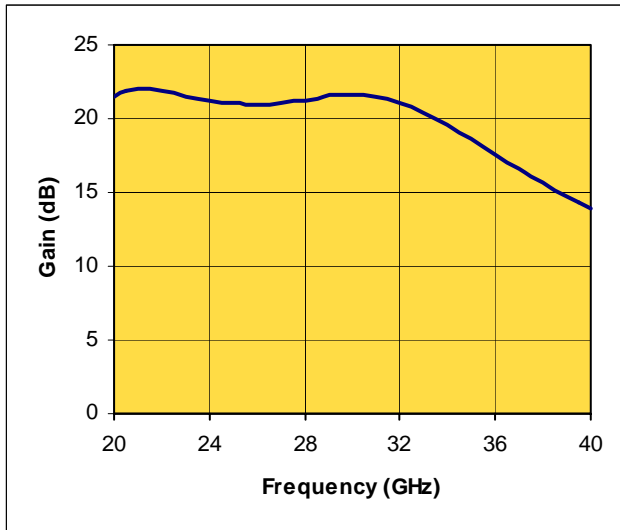
Parameter	Min	Max	Unit
Vd		5.5	V
Id		130	mA
Input drive level		-9	dBm
Assy. Temperature (60 seconds)		300	deg. C

Note: The data contained in this document is for information only. Northrop Grumman reserves the right to change without notice the specifications, designs, prices or conditions of sale, as they apply to this product. The product represented by this datasheet is subject to U.S. Export Law as contained in ITAR or the EAR regulations.

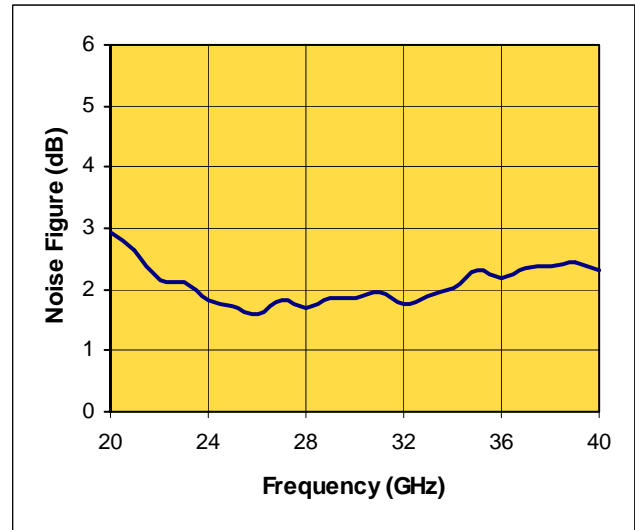


Measured Performance Characteristics (Typical Performance at 25°C)
 Vd = 5.0 V, Id = 68 mA

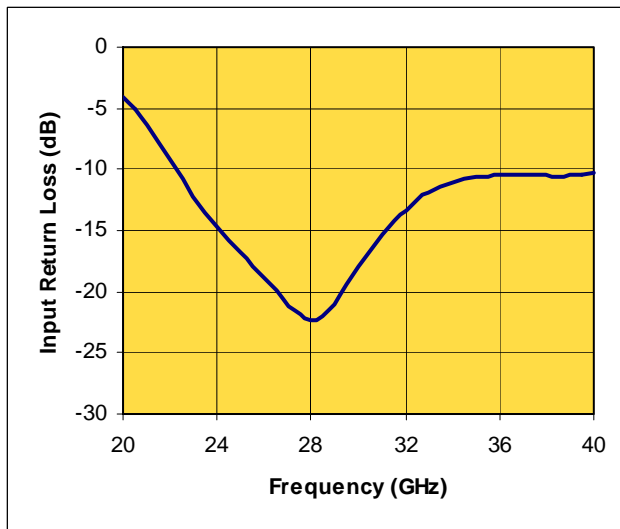
Linear Gain Versus Frequency



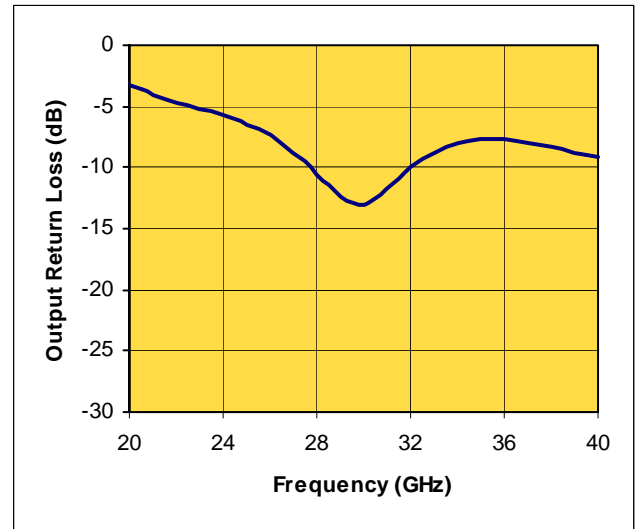
Noise Figure Versus Frequency



Input Return Loss Versus Frequency



Output Return Loss Versus Frequency



Note: The data contained in this document is for information only. Northrop Grumman reserves the right to change without notice the specifications, designs, prices or conditions of sale, as they apply to this product. The product represented by this datasheet is subject to U.S. Export Law as contained in ITAR or the EAR regulations.



Product Datasheet

Revision: May 2007

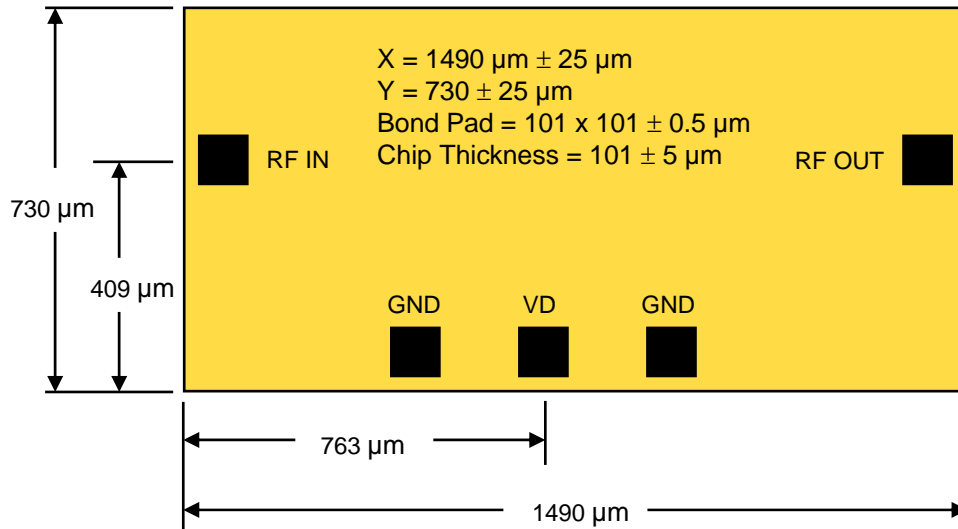
Measured Performance Characteristics (Typical Performance at 25°C)
Vd = 5.0 V, Id = 68 mA

Freq GHz	S11 Mag	S11 Ang	S21 Mag	S21 Ang	S12 Mag	S12 Ang	S22 Mag	S22 Ang
20.00	0.63	141.97	11.81	161.72	0.00	117.15	0.69	-81.92
21.00	0.48	126.11	12.71	124.52	0.00	24.86	0.63	-86.22
22.00	0.34	116.03	12.43	92.49	0.00	-34.00	0.58	-90.64
23.00	0.25	110.95	11.85	65.83	0.00	-74.56	0.55	-96.24
24.00	0.19	108.08	11.46	42.38	0.00	-95.62	0.52	-103.97
25.00	0.14	103.25	11.28	21.23	0.00	-98.38	0.48	-113.94
26.00	0.11	94.17	11.17	1.00	0.01	-121.43	0.43	-126.97
27.00	0.09	72.24	11.27	-18.35	0.01	-128.65	0.37	-143.22
28.00	0.08	38.17	11.58	-37.91	0.01	-139.39	0.30	-167.00
29.00	0.09	1.39	11.97	-58.55	0.01	-160.80	0.24	160.05
30.00	0.13	-28.97	12.07	-80.63	0.01	-178.44	0.23	115.93
31.00	0.17	-49.40	11.85	-102.25	0.01	168.94	0.26	73.81
32.00	0.22	-66.61	11.32	-123.99	0.01	155.90	0.32	41.41
33.00	0.26	-82.25	10.49	-145.11	0.01	139.74	0.36	15.70
34.00	0.28	-94.05	9.53	-164.38	0.01	126.35	0.40	-3.86
35.00	0.29	-103.90	8.52	177.42	0.01	124.21	0.41	-19.78
36.00	0.30	-111.40	7.55	161.01	0.01	110.84	0.41	-33.87
37.00	0.30	-117.85	6.77	146.40	0.01	112.96	0.40	-45.48
38.00	0.30	-121.92	6.06	132.52	0.01	113.97	0.38	-55.47
39.00	0.30	-125.07	5.46	119.59	0.01	95.98	0.37	-65.73
40.00	0.31	-126.49	4.98	107.69	0.01	111.51	0.35	-75.01
41.00	0.31	-128.24	4.58	95.78	0.01	107.71	0.33	-83.74
42.00	0.32	-130.61	4.19	84.12	0.01	104.66	0.31	-93.36
43.00	0.33	-130.36	3.84	74.80	0.01	112.16	0.29	-101.63
44.00	0.34	-131.44	3.66	65.45	0.01	94.66	0.27	-112.94
45.00	0.37	-132.55	3.50	54.38	0.02	97.26	0.26	-123.11

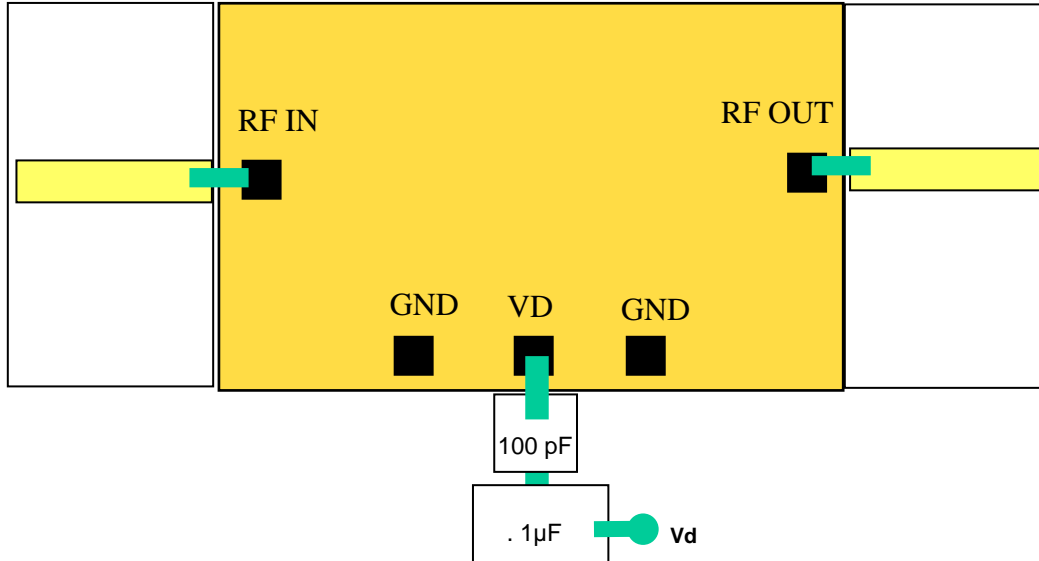
Note: The data contained in this document is for information only. Northrop Grumman reserves the right to change without notice the specifications, designs, prices or conditions of sale, as they apply to this product. The product represented by this datasheet is subject to U.S. Export Law as contained in ITAR or the EAR regulations.



Die Size and Bond Pad Locations



Suggested Bonding



Recommended Assembly Notes

1. Bypass caps should be 100 pF (approximately) ceramic (single-layer) placed no farther than 30 mils from the amplifier.
2. Best performance obtained from use of <10 mil (long) by 3 by 0.5 mil ribbons on input and output.

Note: The data contained in this document is for information only. Northrop Grumman reserves the right to change without notice the specifications, designs, prices or conditions of sale, as they apply to this product. The product represented by this datasheet is subject to U.S. Export Law as contained in ITAR or the EAR regulations.